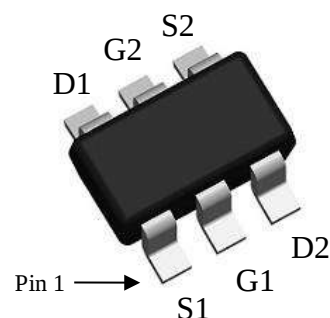


Dual N-Channel Enhancement Mode MOSFET

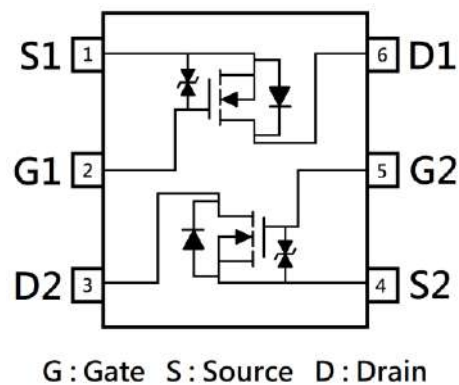
Features:

- ESD protected gate, typical 3kV (HBM)
- High speed switching
- Easily designed drive circuits
- Low-voltage drive
- Easy to use in parallel
- RoHS compliant package

SOT-363



BV_{DSS}	20V
$I_D @ V_{GS}=4.5V, T_A=25^\circ C$	0.63A
$R_{DS(ON) typ.} @ V_{GS}=4.5V, I_D=0.2A$	0.32Ω
$R_{DS(ON) typ.} @ V_{GS}=2.5V, I_D=0.2A$	0.4Ω
$R_{DS(ON) typ.} @ V_{GS}=1.8V, I_D=0.2A$	0.8Ω



Ordering Information

Device	Package	Shipping
KWDK9	SOT-363 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

Absolute Maximum Ratings (T_A=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±8	
Continuous Drain Current @ V _{GS} =4.5V, T _A =25°C	I _D	0.63	A
Continuous Drain Current @ V _{GS} =4.5V, T _A =70°C		0.50	
Pulsed Drain Current *a	I _{DM}	2.5	
Continuous Body Diode Forward Current @ T _A =25°C	I _S	0.2	
ESD susceptibility *b	V _{ESD}	3000	V
Total Power Dissipation @ T _A =25°C	P _D	0.3	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Steady State	Unit
Thermal Resistance, Junction-to-ambient	R _{θJA}	417	°C/W

Note:

*a. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.

*b. Human body model, 1.5kΩ in series with 100pF.

Electrical Characteristics (T_A=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	20	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	0.3	-	1.2		V _{DS} =V _{GS} , I _D =250μA
G _{FS}	-	1	-	S	V _{DS} =5V, I _D =0.2A
I _{GSS}	-	-	±10	μA	V _{GS} =±8V, V _{DS} =0V
I _{DSS}	-	-	1		V _{DS} =16V, V _{GS} =0V
R _{DS(ON)}	-	0.32	0.45	Ω	V _{GS} =4.5V, I _D =0.2A
	-	0.4	0.6		V _{GS} =2.5V, I _D =0.2A
	-	0.8	1.2		V _{GS} =1.8V, I _D =0.2A
Dynamic					
C _{iss}	-	32	-	pF	V _{DS} =10V, V _{GS} =0V, f=1MHz
C _{oss}	-	19	-		
C _{rss}	-	17	-		
Q _g *1, 2	-	0.8	-	nC	V _{DS} =10V, I _D =0.2A, V _{GS} =4.5V
Q _{gs} *1, 2	-	0.2	-		
Q _{gd} *1, 2	-	0.15	-		
t _{d(ON)} *1, 2	-	4.8	-	ns	V _{DS} =10V, I _D =0.2A, V _{GS} =4.5V, R _{GS} =10Ω
t _r *1, 2	-	16	-		
t _{d(OFF)} *1, 2	-	20	-		
t _f *1, 2	-	15.6	-		
Source-Drain Diode					
V _{SD} *1	-	0.8	1.2	V	I _S =0.2A, V _{GS} =0V
t _{rr}	-	7	-	ns	I _F =0.2A, dI _F /dt=100A/μs
Q _{rr}	-	1	-	nC	

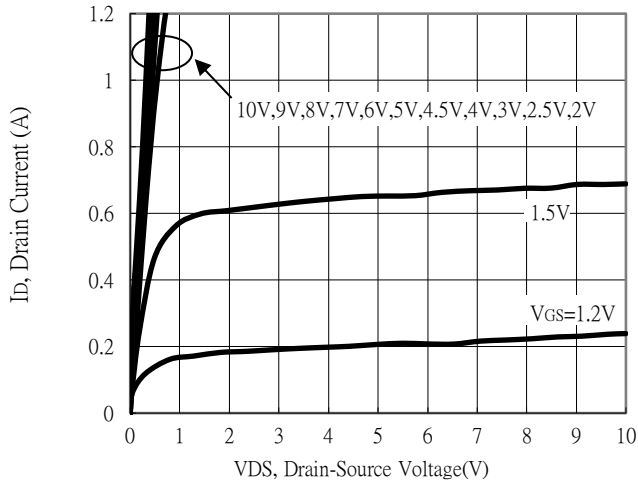
Note:

*1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

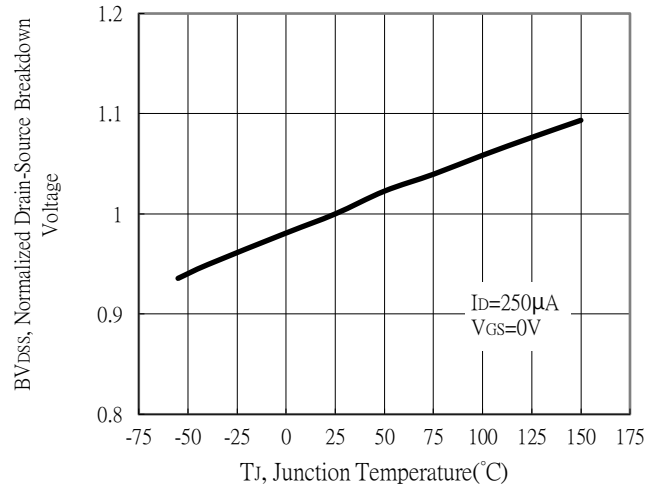
*2. Independent of operating temperature

Typical Characteristics

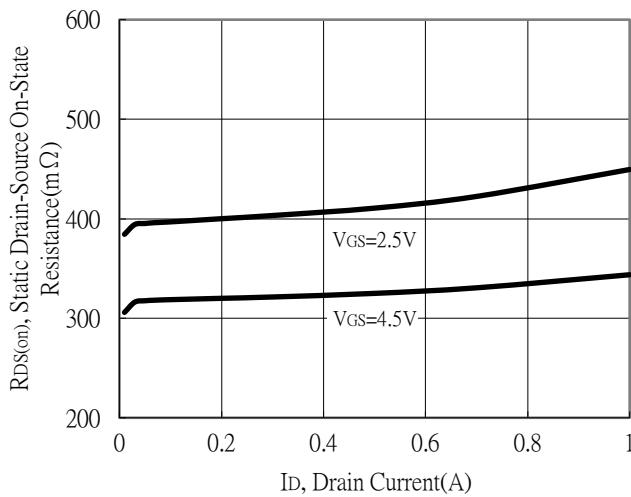
Typical Output Characteristics



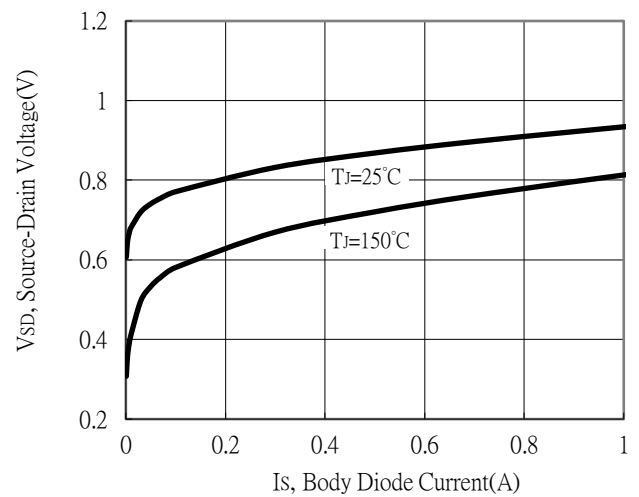
Breakdown Voltage vs Junction Temperature



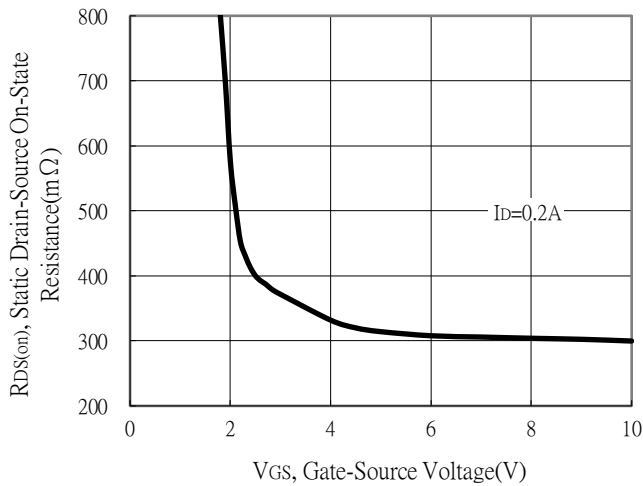
Static Drain-Source On-State resistance vs Drain Current



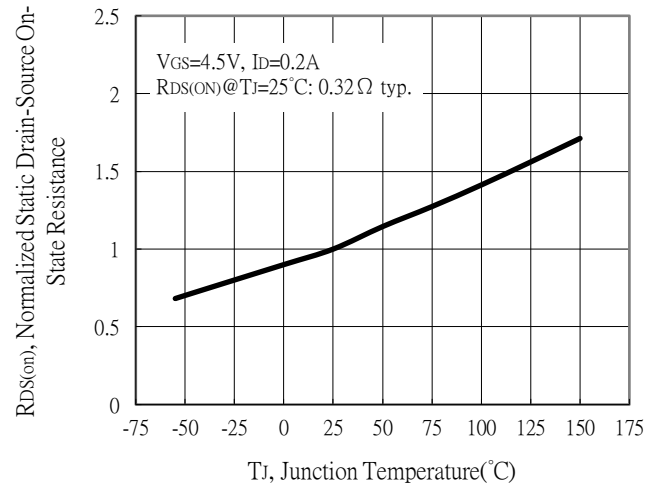
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

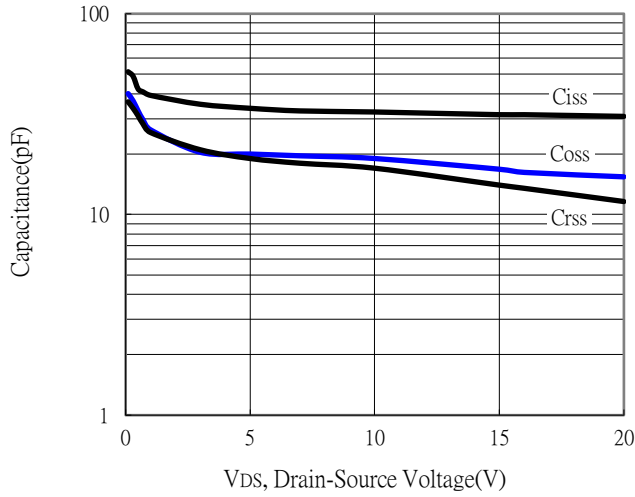


Drain-Source On-State Resistance vs Junction Temperature

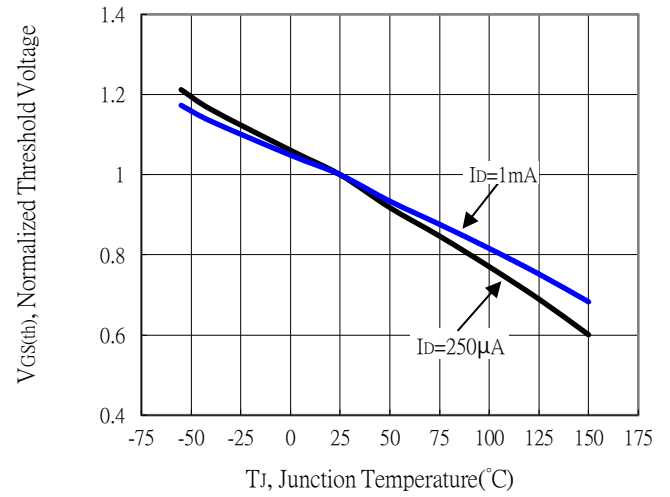


Typical Characteristics (Cont.)

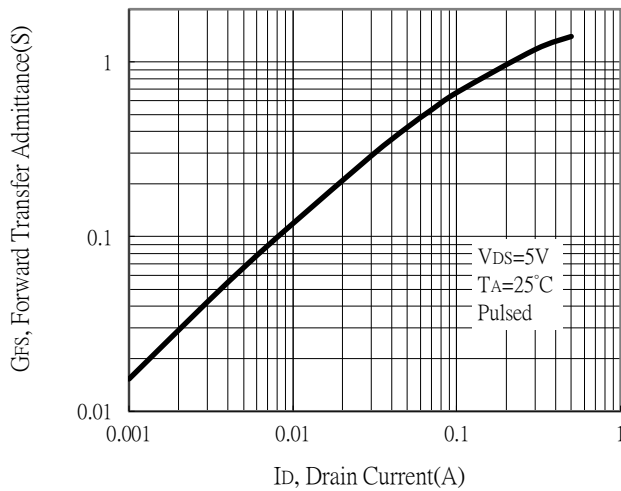
Capacitance vs Drain-to-Source Voltage



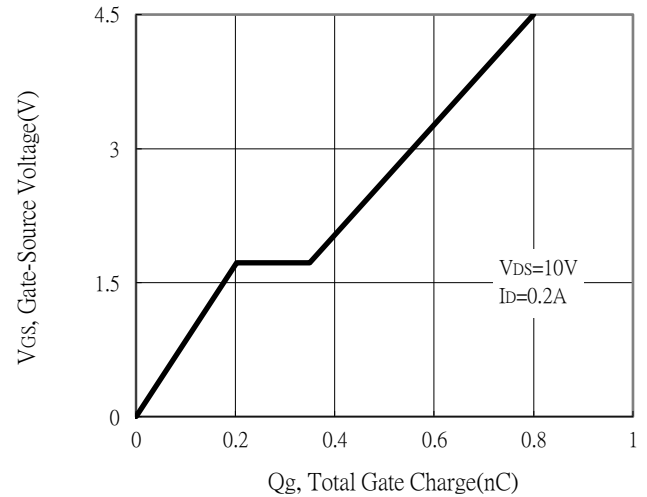
Threshold Voltage vs Junction Temperature



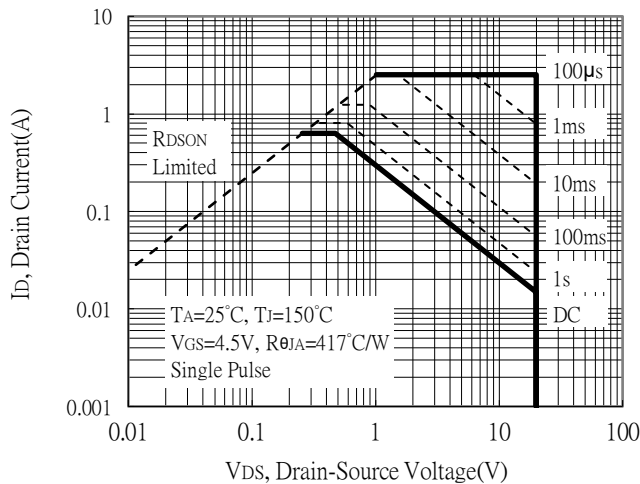
Forward Transfer Admittance vs Drain Current



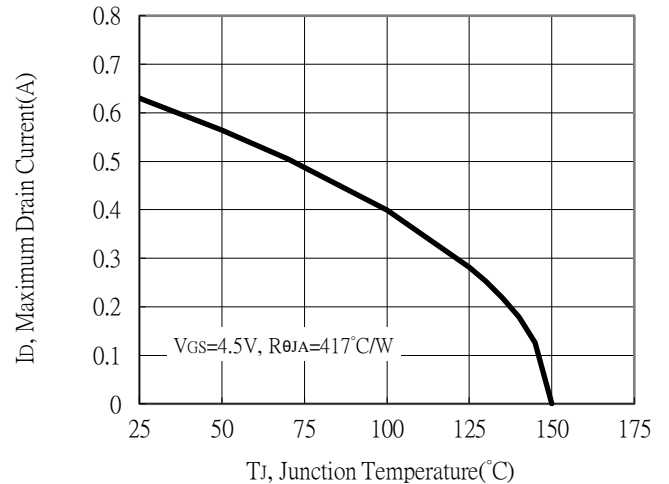
Gate Charge Characteristics



Maximum Safe Operating Area

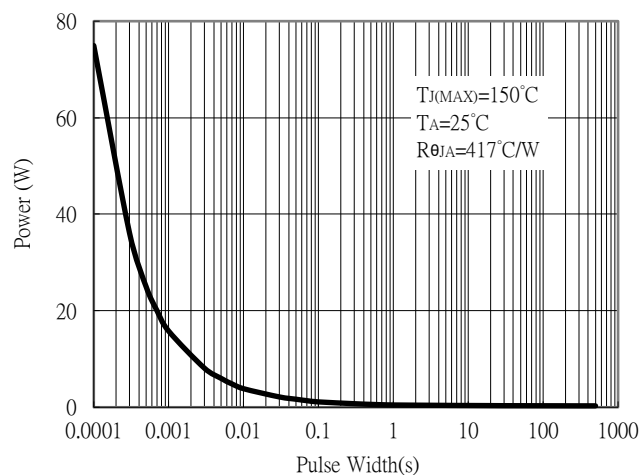


Maximum Drain Current vs Junction Temperature

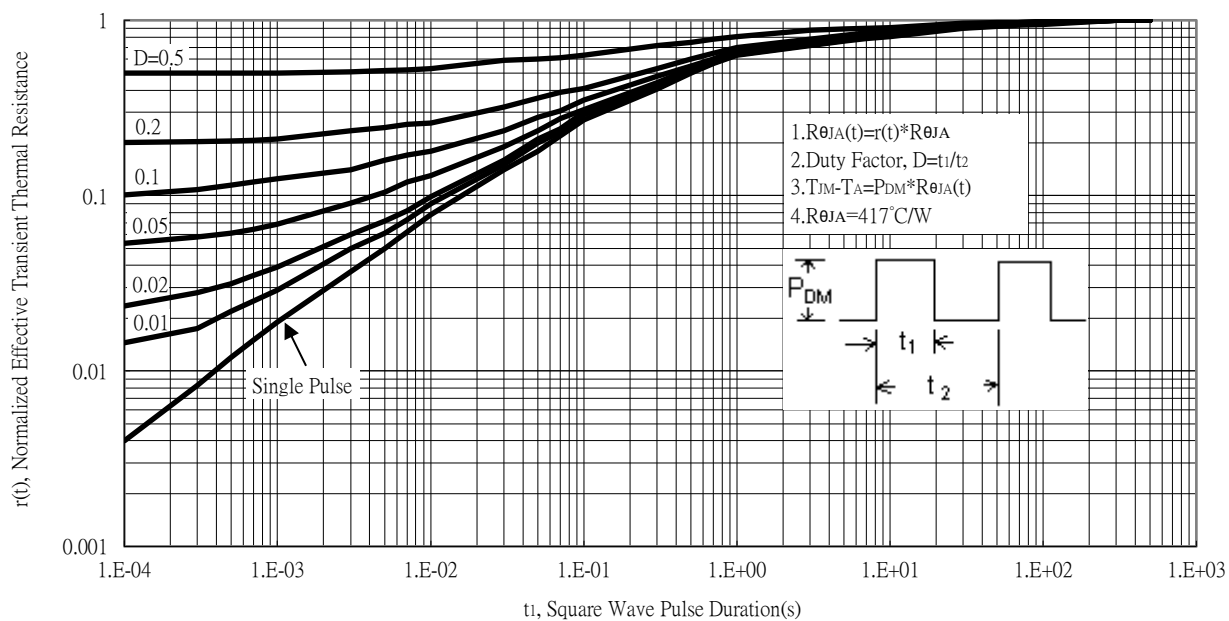


Typical Characteristics (Cont.)

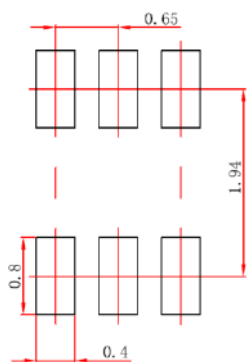
Single Pulse Power Rating, Junction to Ambient



Transient Thermal Response Curves

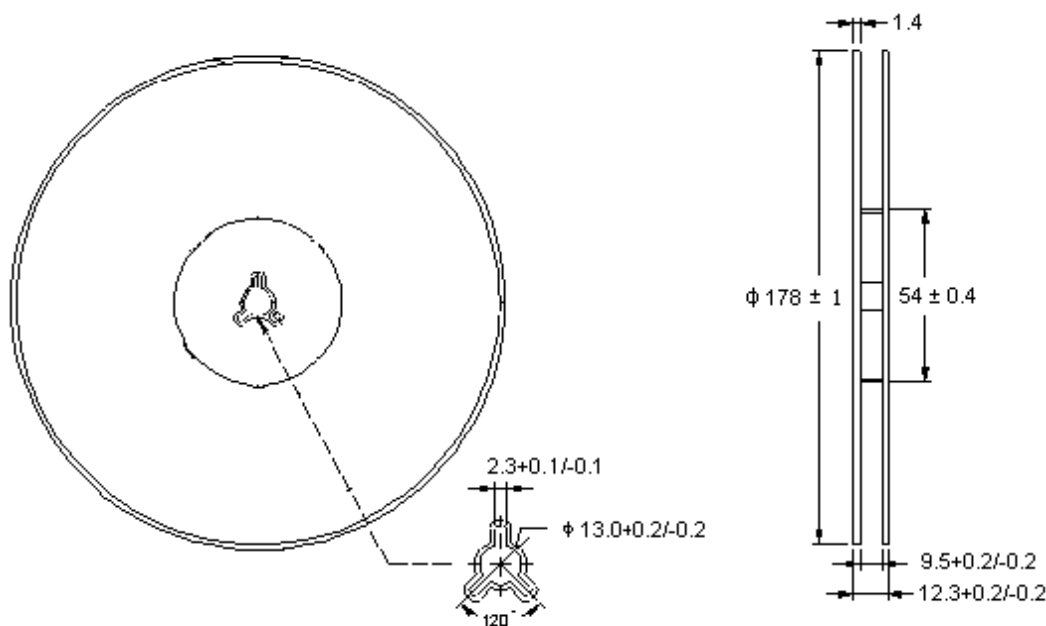


Recommended Soldering Footprint



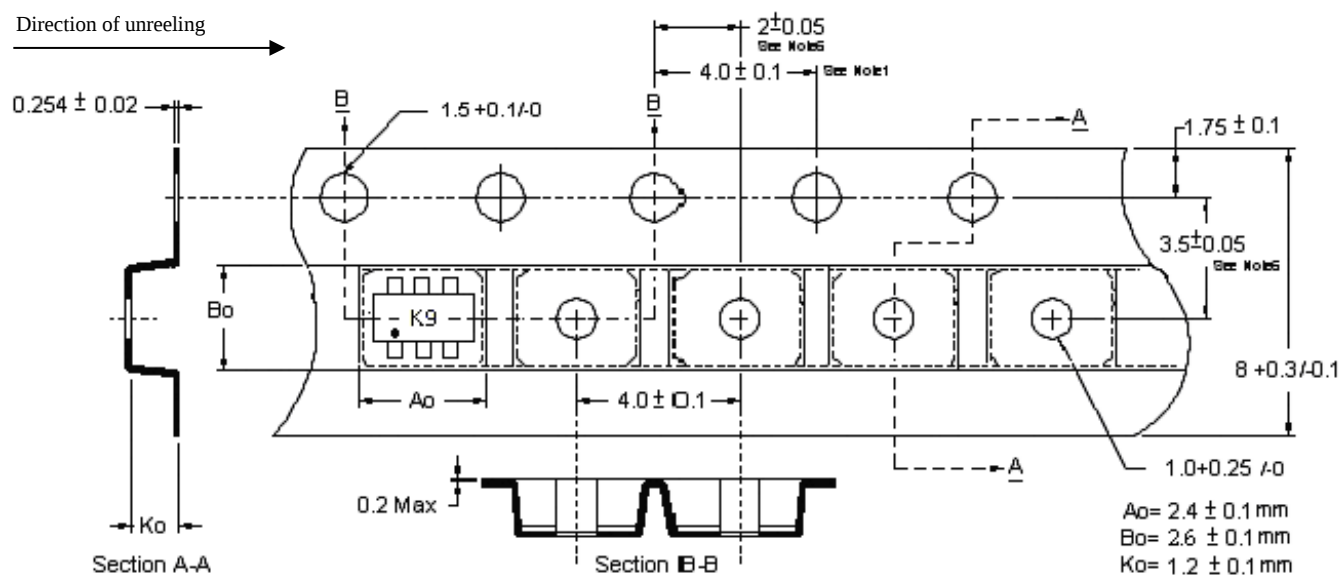
unit:mm

Reel Dimension

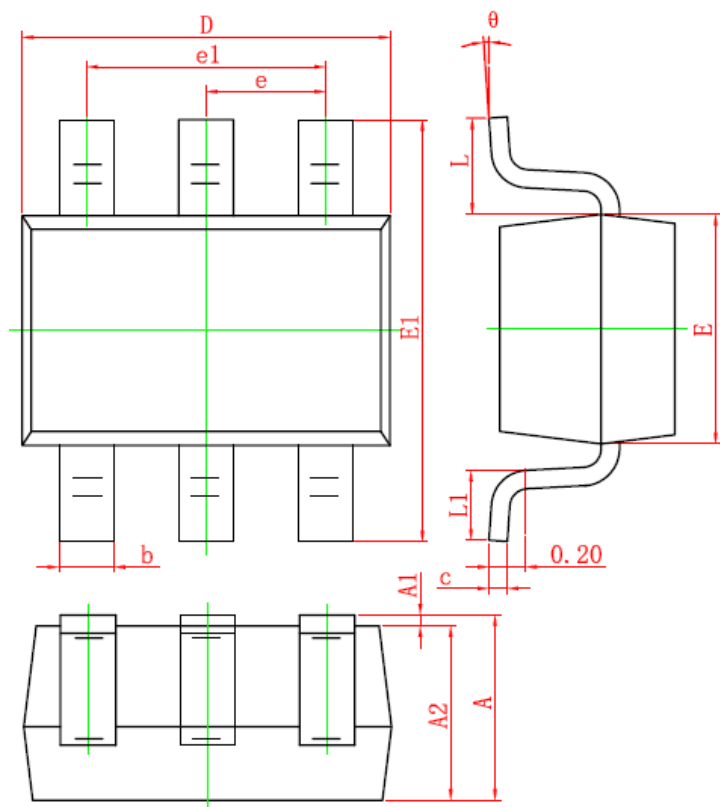


Unit: millimeter

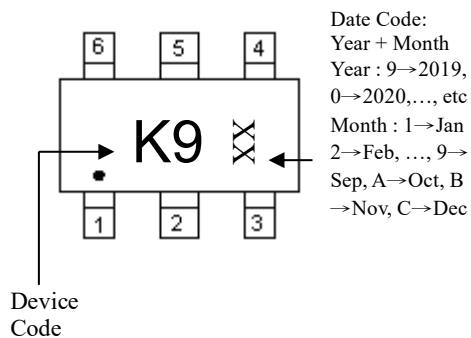
Carrier Tape Dimension



SOT-363 Dimension



Marking:



6-Lead SOT-363 Plastic
Surface Mounted Package

Style:

Pin 1. Source1 (S1)
 Pin 2. Gate1 (G1)
 Pin 3. Drain2 (D2)
 Pin 4. Source2 (S2)
 Pin 5. Gate2 (G2)
 Pin 6. Drain1 (D1)

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	E1	2.150	2.450	0.085	0.096
A1	0.000	0.100	0.000	0.004	e	0.650	TYP	0.026	TYP
A2	0.900	1.000	0.035	0.039	e1	1.200	1.400	0.047	0.055
b	0.150	0.350	0.006	0.014	L	0.525	REF	0.021	REF
c	0.080	0.150	0.003	0.006	L1	0.260	0.460	0.010	0.018
D	2.000	2.200	0.079	0.087	θ	0°	8°	0°	8°
E	1.150	1.350	0.045	0.053					